Quad 2-input NAND Schmitt trigger Rev. 3 — 30 August 2012

Product data sheet

#### 1. **General description**

The 74HC132; 74HCT132 is a high-speed Si-gate CMOS device and is pin compatible with Low-power Schottky TTL (LSTTL). It is specified in compliance with JEDEC standard No. 7A

The 74HC132; 74HCT132 is a quad 2-input NAND gate with Schmitt trigger inputs. This device features reduced input threshold levels to allow interfacing to TTL logic levels. Inputs also include clamp diodes that enable the use of current limiting resistors to interface inputs to voltages in excess of V<sub>CC</sub>. Schmitt trigger inputs transform slowly changing input signals into sharply defined jitter-free output signals.

The inputs switch at different points for positive and negative-going signals. The difference between the positive voltage  $V_{T+}$  and the negative voltage  $V_{T-}$  is defined as the input hysteresis voltage V<sub>H</sub>.

#### **Features and benefits** 2.

- ESD protection:
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from –40 °C to +85 °C and from –40 °C to +125 °C

#### **Applications** 3.

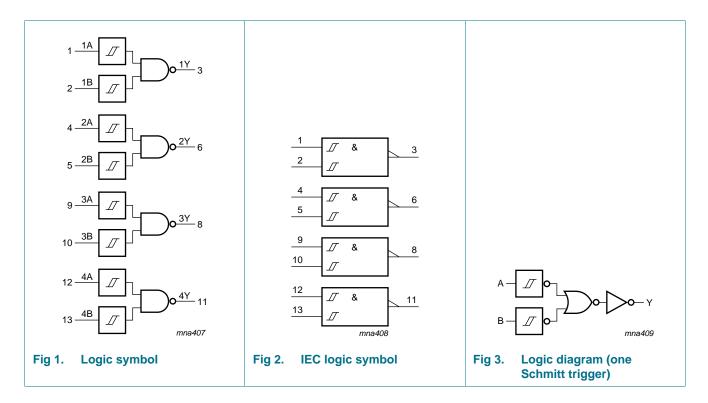
- Wave and pulse shapers
- Astable multivibrators
- Monostable multivibrators



### 4. Ordering information

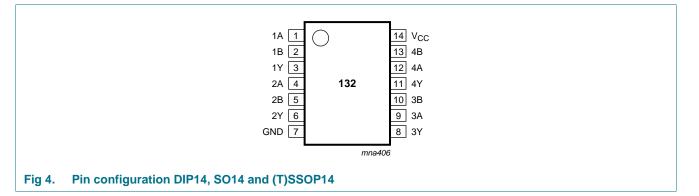
| Type number | Package           |   |  |            |  |
|-------------|-------------------|---|--|------------|--|
|             | Temperature range | Name  | Description  | Version    |  |
| 74HC132N    | –40 °C to +125 °C | DIP14   | plastic dual in-line package; 14 leads (300 mil)     | SOT27-1    |  |
| 74HCT132N   |                   |   |  |            |  |
| 74HC132D    | –40 °C to +125 °C | to +125 °C SO14 plastic small outline package; 14 leads; body |  | h SOT108-1 |  |
| 74HCT132D   |                   |   | 3.9 mm   |            |  |
| 74HC132DB   | –40 °C to +125 °C | SSOP14  | plastic shrink small outline package; 14 leads; body | SOT337-    |  |
| 74HCT132DB  |                   |   | width 5.3 mm   |            |  |
| 74HC132PW   | –40 °C to +125 °C | TSSOP14   | plastic thin shrink small outline package; 14 leads; | SOT402-    |  |
| 74HCT132PW  |                   |   | body width 4.4 mm                                    |            |  |

### 5. Functional diagram



### 6. Pinning information

### 6.1 Pinning



### 6.2 Pin description

| Table 2.        | Pin description |                |
|-----------------|-----------------|----------------|
| Symbol          | Pin             | Description    |
| 1A to 4A        | 1, 4, 9, 12     | data input     |
| 1B to 4B        | 2, 5, 10, 13    | data input     |
| 1Y to 4Y        | 3, 6, 8, 11     | data output    |
| GND             | 7               | ground (0 V)   |
| V <sub>CC</sub> | 14              | supply voltage |

## 7. Functional description

#### Table 3.Function table

| Input |    | Output |
|-------|----|--------|
| nA    | nB | nY     |
| L     | L  | Н      |
| L     | Н  | Н      |
| Н     | L  | Н      |
| Н     | Н  | L      |

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care.

### 8. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

|                  | _                            |   |              |      |      |
|------------------|------------------------------|---|--------------|------|------|
| Symbol           | Parameter                    | Conditions  | Min          | Max  | Unit |
| V <sub>CC</sub>  | supply voltage               |   | -0.5         | +7   | V    |
| I <sub>IK</sub>  | input clamping current       | $V_{\rm I}$ < –0.5 V or $V_{\rm I}$ > $V_{\rm CC}$ + 0.5 V            | <u>[1]</u> _ | ±20  | mA   |
| I <sub>OK</sub>  | output clamping current      | $V_{O}$ < –0.5 V or $V_{O}$ > $V_{CC}$ + 0.5 V                        | <u>[1]</u> _ | ±20  | mA   |
| I <sub>O</sub>   | output current               | $-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}}$ + 0.5 V | -            | ±25  | mA   |
| I <sub>CC</sub>  | supply current               |   | -            | 50   | mA   |
| I <sub>GND</sub> | ground current               |   | -50          | -    | mA   |
| T <sub>stg</sub> | storage temperature          |   | -65          | +150 | °C   |
| P <sub>tot</sub> | total power dissipation      |   | [2]          |      |      |
|                  | DIP14 package                |   | -            | 750  | mW   |
|                  | SO14, and (T)SSOP14 packages |   | -            | 500  | mW   |

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

For DIP14 package: P<sub>tot</sub> derates linearly with 12 mW/K above 70 °C.
 For SO14 package: P<sub>tot</sub> derates linearly with 8 mW/K above 70 °C.
 For (T)SSOP14 packages: P<sub>tot</sub> derates linearly with 5.5 mW/K above 60 °C.

### 9. Recommended operating conditions

#### Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

| Symbol           | ol Parameter Conditions 74HC13 |  | HC132 |     | 74HCT132 |     |     | Unit            |    |
|------------------|--------------------------------|--|-------|-----|----------|-----|-----|-----------------|----|
|                  |                                |  | Min   | Тур | Max      | Min | Тур | Max             |    |
| V <sub>CC</sub>  | supply voltage                 |  | 2.0   | 5.0 | 6.0      | 4.5 | 5.0 | 5.5             | V  |
| VI               | input voltage                  |  | 0     | -   | $V_{CC}$ | 0   | -   | V <sub>CC</sub> | V  |
| Vo               | output voltage                 |  | 0     | -   | $V_{CC}$ | 0   | -   | V <sub>CC</sub> | V  |
| T <sub>amb</sub> | ambient temperature            |  | -40   | +25 | +125     | -40 | +25 | +125            | °C |

## **10. Static characteristics**

#### Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

| Symbol           | Parameter                 | Conditions  |      | 25 °C |      | –40 °C to +85 °C |      | –40 °C to +125 °C |      | Uni |
|------------------|---------------------------|---|------|-------|------|------------------|------|-------------------|------|-----|
|                  |                           |   | Min  | Тур   | Max  | Min              | Max  | Min               | Max  |     |
| 74HC13           | 2                         |   |      |       |      |                  |      |                   |      |     |
| V <sub>OH</sub>  | HIGH-level                | $V_I = V_{T+} \text{ or } V_{T-}$   |      |       |      |                  |      |                   |      |     |
|                  | output voltage            | $I_O = -20 \ \mu\text{A}; \ V_{CC} = 2.0 \ \text{V}$  | 1.9  | 2.0   | -    | 1.9              | -    | 1.9               | -    | V   |
|                  |                           | $I_O = -20 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$  | 4.4  | 4.5   | -    | 4.4              | -    | 4.4               | -    | V   |
|                  |                           | $I_0 = -20 \ \mu A; \ V_{CC} = 6.0 \ V$   | 5.9  | 6.0   | -    | 5.9              | -    | 5.9               | -    | V   |
|                  |                           | $I_{O}$ = -4.0 mA; $V_{CC}$ = 4.5 V   | 3.98 | 4.32  | -    | 3.84             | -    | 3.7               | -    | V   |
|                  |                           | $I_{O}$ = -5.2 mA; $V_{CC}$ = 6.0 V   | 5.48 | 5.81  | -    | 5.34             | -    | 5.2               | -    | V   |
| V <sub>OL</sub>  | LOW-level                 | $V_I = V_{T+} \text{ or } V_{T-}$   |      |       |      |                  |      |                   |      |     |
|                  | output voltage            | $I_O = 20 \ \mu\text{A}; \ V_{CC} = 2.0 \ \text{V}$   | -    | 0     | 0.1  | -                | 0.1  | -                 | 0.1  | V   |
|                  |                           | $I_O = 20 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$   | -    | 0     | 0.1  | -                | 0.1  | -                 | 0.1  | V   |
|                  |                           | $I_0 = 20 \ \mu A; V_{CC} = 6.0 \ V$  | -    | 0     | 0.1  | -                | 0.1  | -                 | 0.1  | V   |
|                  |                           | $I_{O}$ = 4.0 mA; $V_{CC}$ = 4.5 V  | -    | 0.15  | 0.26 | -                | 0.33 | -                 | 0.4  | V   |
|                  |                           | $I_0 = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$  | -    | 0.16  | 0.26 | -                | 0.33 | -                 | 0.4  | V   |
| I                | input leakage current     | $V_I = V_{CC}$ or GND;<br>$V_{CC} = 6.0 V$  | -    | -     | ±0.1 | -                | ±1.0 | -                 | ±1.0 | μA  |
| сс               | supply current            | $V_I = V_{CC}$ or GND; $I_O = 0$ A;<br>$V_{CC} = 6.0$ V   | -    | -     | 2.0  | -                | 20   | -                 | 40   | μA  |
| Cı               | input<br>capacitance      |   | -    | 3.5   | -    | -                | -    | -                 | -    | pF  |
| 74HCT1           | 32                        |   |      |       |      |                  |      |                   |      |     |
| V <sub>OH</sub>  | HIGH-level                | $V_{I} = V_{T+} \text{ or } V_{T-}; V_{CC} = 4.5 \text{ V}$   |      |       |      |                  |      |                   |      |     |
|                  | output voltage            | I <sub>O</sub> = -20 μA   | 4.4  | 4.5   | -    | 4.4              | -    | 4.4               | -    | V   |
|                  |                           | $I_{O} = -4.0 \text{ mA}$   | 3.98 | 4.32  | -    | 3.84             | -    | 3.7               | -    | V   |
| V <sub>OL</sub>  | LOW-level                 | $V_I = V_{T+}$ or $V_{T-}$ ; $V_{CC} = 4.5 \text{ V}$   |      |       |      |                  |      |                   |      |     |
|                  | output voltage            | I <sub>O</sub> = 20 μA;   | -    | 0     | 0.1  | -                | 0.1  | -                 | 0.1  | V   |
|                  |                           | l <sub>O</sub> = 4.0 mA;  | -    | 0.15  | 0.26 | -                | 0.33 | -                 | 0.4  | V   |
| I                | input leakage<br>current  | $V_I = V_{CC}$ or GND;<br>$V_{CC} = 5.5 V$  | -    | -     | ±0.1 | -                | ±1.0 | -                 | ±1.0 | μA  |
| сс               | supply current            | $V_I = V_{CC}$ or GND; $I_O = 0$ A;<br>$V_{CC} = 5.5$ V   | -    | -     | 2.0  | -                | 20   | -                 | 40   | μA  |
| ∆l <sub>CC</sub> | additional supply current | per input pin;<br>$V_I = V_{CC} - 2.1 \text{ V}; I_O = 0 \text{ A};$<br>other inputs at $V_{CC}$ or GND;<br>$V_{CC} = 4.5 \text{ V}$ to 5.5 V | -    | 30    | 108  | -                | 135  | -                 | 147  | μΑ  |
| CI               | input<br>capacitance      |   | -    | 3.5   | -    | -                | -    | -                 | -    | pF  |

### **11. Dynamic characteristics**

#### Table 7. Dynamic characteristics

GND = 0 V;  $C_L = 50$  pF; for load circuit see <u>Figure 6</u>.

| Symbol                         | Parameter                     | Conditions  |            |     | 25 °C |     | -40 °C to      | –40 °C to +125 °C |    |  |
|--------------------------------|-------------------------------|---|------------|-----|-------|-----|----------------|-------------------|----|--|
|                                |                               |   |            | Min | Тур   | Max | Мах<br>(85 °С) | Max<br>(125 °C)   |    |  |
| 74HC132                        | 2                             |   | 1          |     |       |     |                |                   |    |  |
| t <sub>pd</sub>                | propagation delay             | nA, nB to nY; see <u>Figure 5</u>                                   | <u>[1]</u> |     |       |     |                |                   |    |  |
|                                |                               | $V_{CC} = 2.0 V$  |            | -   | 36    | 125 | 155            | 190               | ns |  |
|                                |                               | $V_{CC} = 4.5 V$  |            | -   | 13    | 25  | 31             | 38                | ns |  |
|                                |                               | $V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$             |            | -   | 11    | -   | -              | -                 | ns |  |
|                                |                               | $V_{CC} = 6.0 V$  |            | -   | 10    | 21  | 26             | 32                | ns |  |
| t <sub>t</sub> transition time | transition time               | see <u>Figure 5</u>   | [2]        |     |       |     |                |                   |    |  |
|                                |                               | $V_{CC} = 2.0 V$  |            | -   | 19    | 75  | 95             | 110               | ns |  |
|                                |                               | $V_{CC} = 4.5 V$  |            | -   | 7     | 15  | 19             | 22                | ns |  |
|                                |                               | $V_{CC} = 6.0 V$  |            | -   | 6     | 13  | 16             | 19                | ns |  |
| C <sub>PD</sub>                | power dissipation capacitance | per package; $V_I = GND$ to $V_{CC}$                                | <u>[3]</u> | -   | 24    | -   | -              | -                 | pF |  |
| 74HCT1:                        | 32                            |   |            |     |       |     |                |                   |    |  |
| t <sub>pd</sub>                | propagation delay             | nA, nB to nY; see <u>Figure 5</u>                                   | <u>[1]</u> |     |       |     |                |                   |    |  |
|                                |                               | $V_{CC} = 4.5 V$  |            | -   | 20    | 33  | 41             | 50                | ns |  |
|                                |                               | $V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$             |            | -   | 17    | -   | -              | -                 | ns |  |
| t <sub>t</sub>                 | transition time               | $V_{CC} = 4.5 \text{ V}; \text{ see } \frac{\text{Figure 5}}{1000}$ | [2]        | -   | 7     | 15  | 19             | 22                | ns |  |
| C <sub>PD</sub>                | power dissipation capacitance | per package;<br>V <sub>I</sub> = GND to V <sub>CC</sub> – 1.5 V     | <u>[3]</u> | -   | 20    | -   | -              | -                 | pF |  |

[1]  $t_{pd}$  is the same as  $t_{PHL}$  and  $t_{PLH}$ .

[2]  $t_t$  is the same as  $t_{THL}$  and  $t_{TLH}$ .

[3]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ):

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \sum (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$ 

 $f_i$  = input frequency in MHz;

 $f_o = output frequency in MHz;$ 

 $C_L$  = output load capacitance in pF;

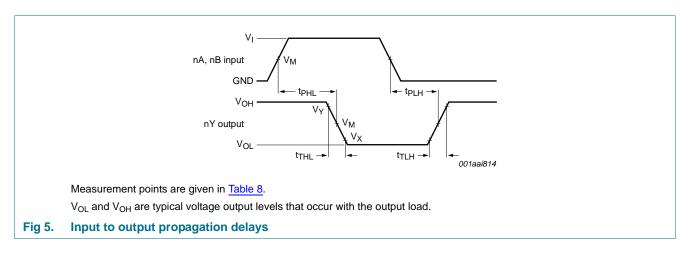
 $V_{CC}$  = supply voltage in V;

N = number of inputs switching;

 $\Sigma~(C_L \times V_{CC}{}^2 \times f_o)$  = sum of outputs.

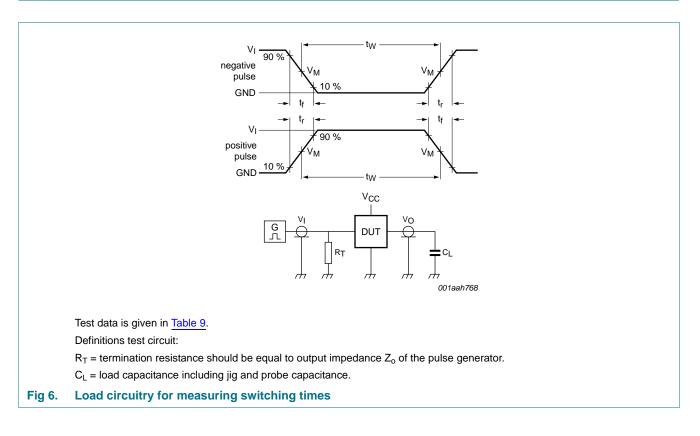
**Quad 2-input NAND Schmitt trigger** 

### 12. Waveforms



#### Table 8. **Measurement points**

| Туре     | Input              | Output             |                    |                    |  |  |
|----------|--------------------|--------------------|--------------------|--------------------|--|--|
|          | V <sub>M</sub>     | V <sub>M</sub>     | V <sub>X</sub>     | V <sub>Y</sub>     |  |  |
| 74HC132  | 0.5V <sub>CC</sub> | 0.5V <sub>CC</sub> | 0.1V <sub>CC</sub> | 0.9V <sub>CC</sub> |  |  |
| 74HCT132 | 1.3 V              | 1.3 V              | 0.1V <sub>CC</sub> | 0.9V <sub>CC</sub> |  |  |



74HC\_HCT132 **Product data sheet** 

## 74HC132; 74HCT132

#### Quad 2-input NAND Schmitt trigger

| Table 9. Test data |                 |                                 |              |                                     |
|--------------------|-----------------|---------------------------------|--------------|-------------------------------------|
| Туре               | Input L         |                                 |              | Test                                |
|                    | VI              | t <sub>r</sub> , t <sub>f</sub> | CL           |                                     |
| 74HC132            | V <sub>CC</sub> | 6.0 ns                          | 15 pF, 50 pF | t <sub>PLH</sub> , t <sub>PHL</sub> |
| 74HCT132           | 3.0 V           | 6.0 ns                          | 15 pF, 50 pF | t <sub>PLH</sub> , t <sub>PHL</sub> |

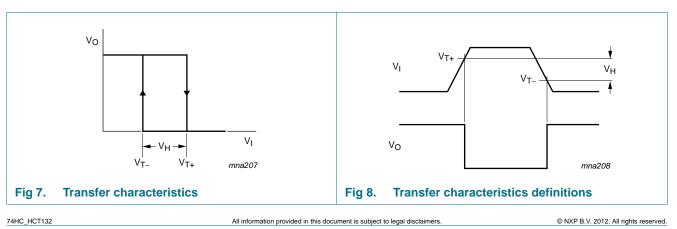
### **13. Transfer characteristics**

#### Table 10. Transfer characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); see <u>Figure 7</u> and <u>Figure 8</u>.

| Symbol          | Parameter            | Conditions              | Ta  | <sub>mb</sub> = 25 | °C   | T <sub>amb</sub> = −40 °C<br>to +85 °C |      | T <sub>amb</sub> = −40 °C<br>to +125 °C |      | Unit |
|-----------------|----------------------|-------------------------|-----|--------------------|------|--|------|---|------|------|
|                 |                      | Min                     | Тур | Max                | Min  | Max                                    | Min  | Max                                     |      |      |
| 74HC13          | 2                    |                         |     |                    |      |  |      |   |      |      |
| V <sub>T+</sub> | positive-going       | $V_{CC} = 2.0 V$        | 0.7 | 1.18               | 1.5  | 0.7                                    | 1.5  | 0.7                                     | 1.5  | V    |
|                 | threshold            | $V_{CC} = 4.5 V$        | 1.7 | 2.38               | 3.15 | 1.7                                    | 3.15 | 1.7                                     | 3.15 | V    |
|                 | voltage              | $V_{CC} = 6.0 V$        | 2.1 | 3.14               | 4.2  | 2.1                                    | 4.2  | 2.1                                     | 4.2  | V    |
| $V_{T-}$        | negative-going       | $V_{CC} = 2.0 V$        | 0.3 | 0.63               | 1.0  | 0.3                                    | 1.0  | 0.3                                     | 1.0  | V    |
|                 | threshold            | $V_{CC} = 4.5 V$        | 0.9 | 1.67               | 2.2  | 0.9                                    | 2.2  | 0.9                                     | 2.2  | V    |
|                 | voltage              | $V_{CC} = 6.0 V$        | 1.2 | 2.26               | 3.0  | 1.2                                    | 3.0  | 1.2                                     | 3.0  | V    |
| V <sub>H</sub>  | hysteresis           | $V_{CC} = 2.0 V$        | 0.2 | 0.55               | 1.0  | 0.2                                    | 1.0  | 0.2                                     | 1.0  | V    |
|                 | voltage              | $V_{CC} = 4.5 V$        | 0.4 | 0.71               | 1.4  | 0.4                                    | 1.4  | 0.4                                     | 1.4  | V    |
|                 |                      | $V_{CC} = 6.0 V$        | 0.6 | 0.88               | 1.6  | 0.6                                    | 1.6  | 0.6                                     | 1.6  | V    |
| 74HCT1          | 32                   |                         |     |                    |      |  |      |   |      |      |
| V <sub>T+</sub> | positive-going       | $V_{CC} = 4.5 V$        | 1.2 | 1.41               | 1.9  | 1.2                                    | 1.9  | 1.2                                     | 1.9  | V    |
|                 | threshold<br>voltage | $V_{CC} = 5.5 V$        | 1.4 | 1.59               | 2.1  | 1.4                                    | 2.1  | 1.4                                     | 2.1  | V    |
| $V_{T-}$        | negative-going       | $V_{CC} = 4.5 V$        | 0.5 | 0.85               | 1.2  | 0.5                                    | 1.2  | 0.5                                     | 1.2  | V    |
|                 | threshold<br>voltage | $V_{CC} = 5.5 V$        | 0.6 | 0.99               | 1.4  | 0.6                                    | 1.4  | 0.6                                     | 1.4  | V    |
| V <sub>H</sub>  | hysteresis           | $V_{CC} = 4.5 V$        | 0.4 | 0.56               | -    | 0.4                                    | -    | 0.4                                     | -    | V    |
|                 | voltage              | V <sub>CC</sub> = 5.5 V | 0.4 | 0.60               | -    | 0.4                                    | -    | 0.4                                     | -    | V    |

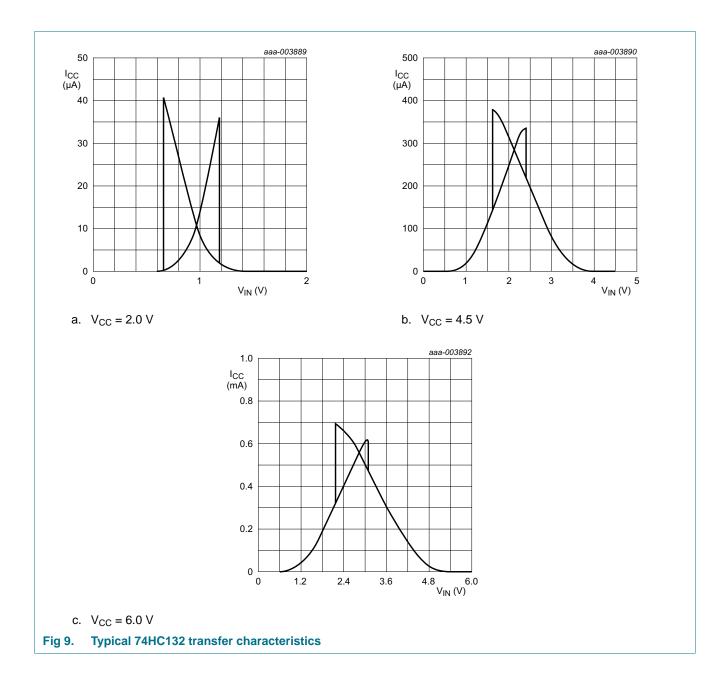
## 14. Transfer characteristics waveforms



Product data sheet

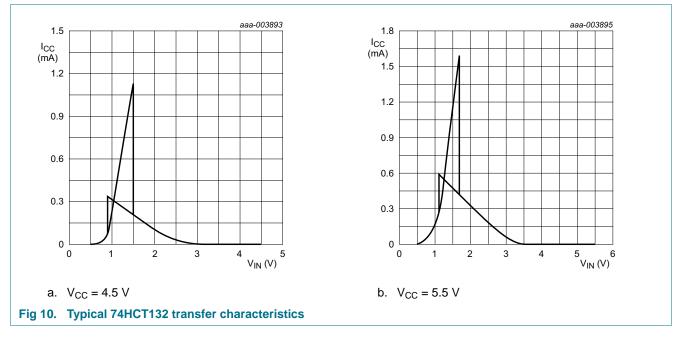
# 74HC132; 74HCT132

Quad 2-input NAND Schmitt trigger



## 74HC132; 74HCT132

**Quad 2-input NAND Schmitt trigger** 



### **15. Application information**

The slow input rise and fall times cause additional power dissipation, this can be calculated using the following formula:

 $P_{add} = f_i \times (t_r \times \Delta I_{CC(AV)} + t_f \times \Delta I_{CC(AV)}) \times V_{CC}$  where:

 $P_{add}$  = additional power dissipation ( $\mu$ W);

 $f_i = input frequency (MHz);$ 

 $t_r$  = rise time (ns); 10 % to 90 %;

t<sub>f</sub> = fall time (ns); 90 % to 10 %;

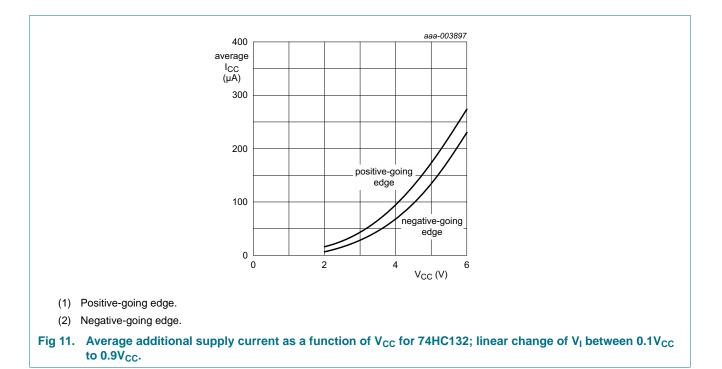
 $\Delta I_{CC(AV)}$  = average additional supply current (µA).

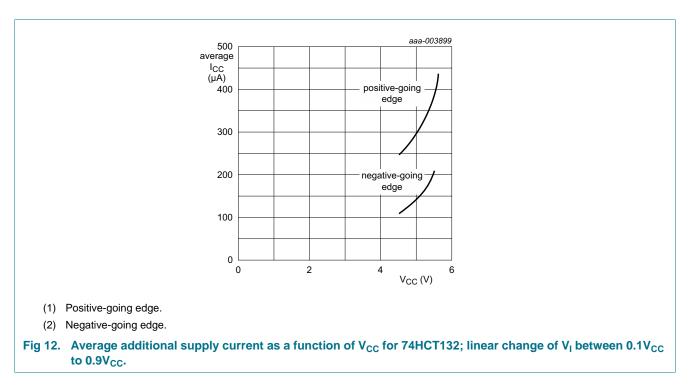
Average  $\Delta I_{CC(AV)}$  differs with positive or negative input transitions, as shown in Figure 11 and Figure 12.

An example of a relaxation circuit using the 74HC132; 74HCT132 is shown in Figure 13.

# 74HC132; 74HCT132

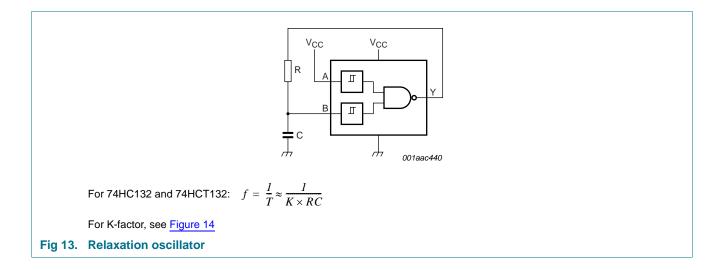
Quad 2-input NAND Schmitt trigger

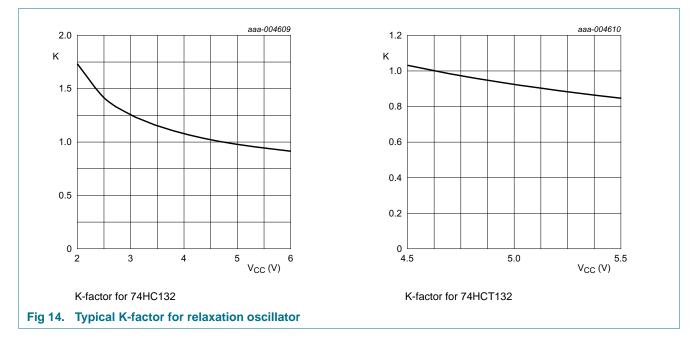




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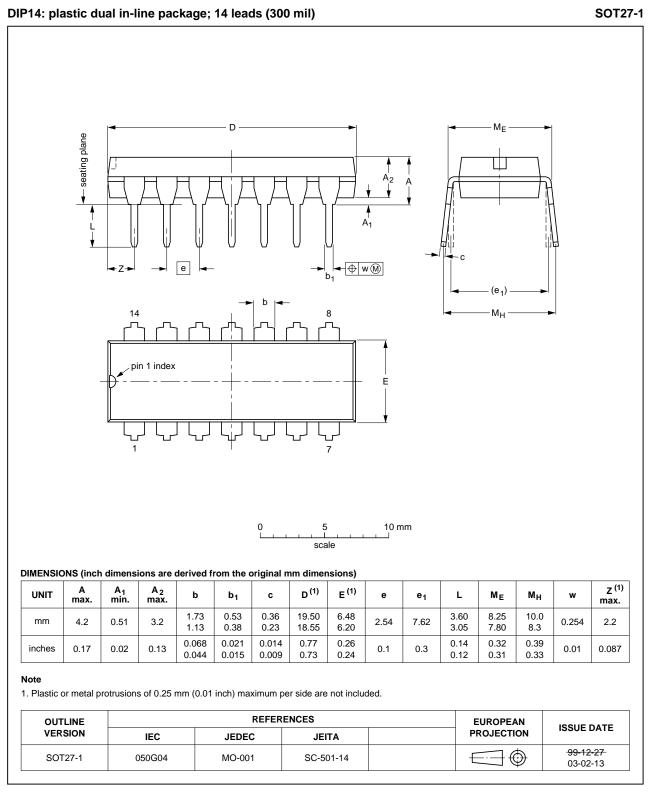
#### Quad 2-input NAND Schmitt trigger





**Quad 2-input NAND Schmitt trigger** 

### 16. Package outline



#### Fig 15. Package outline SOT27-1 (DIP14)

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**Quad 2-input NAND Schmitt trigger** 

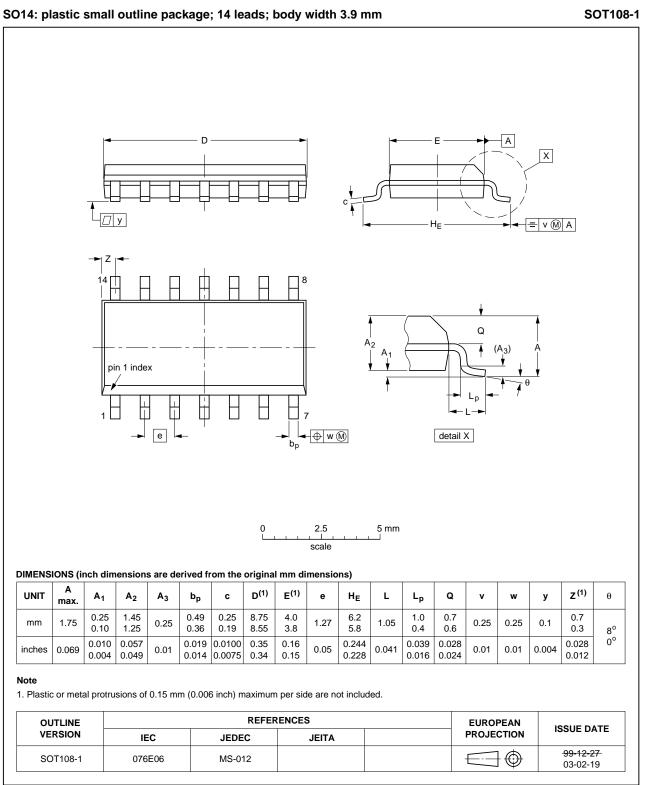


Fig 16. Package outline SOT108-1 (SO14)

**Quad 2-input NAND Schmitt trigger** 

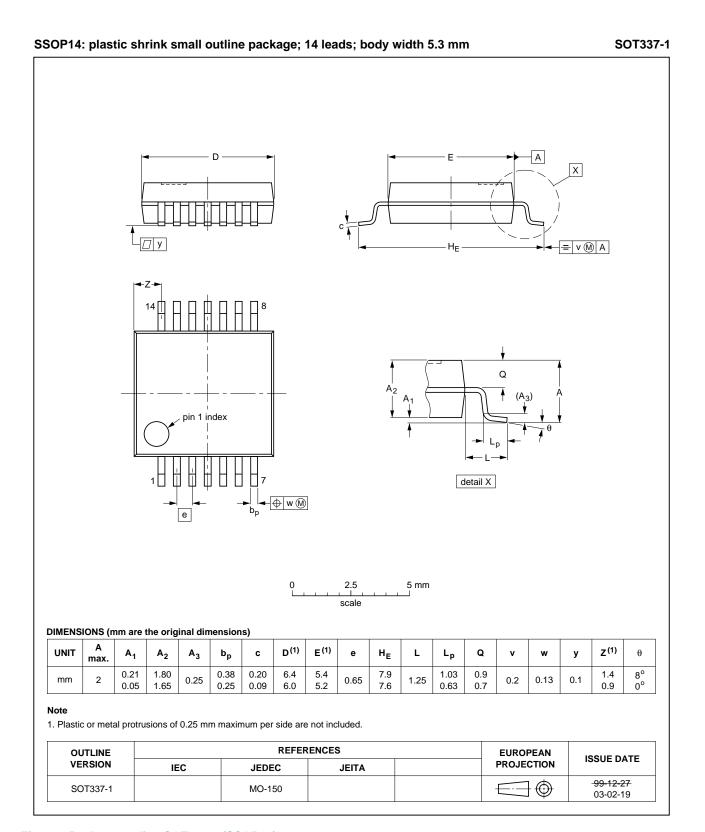
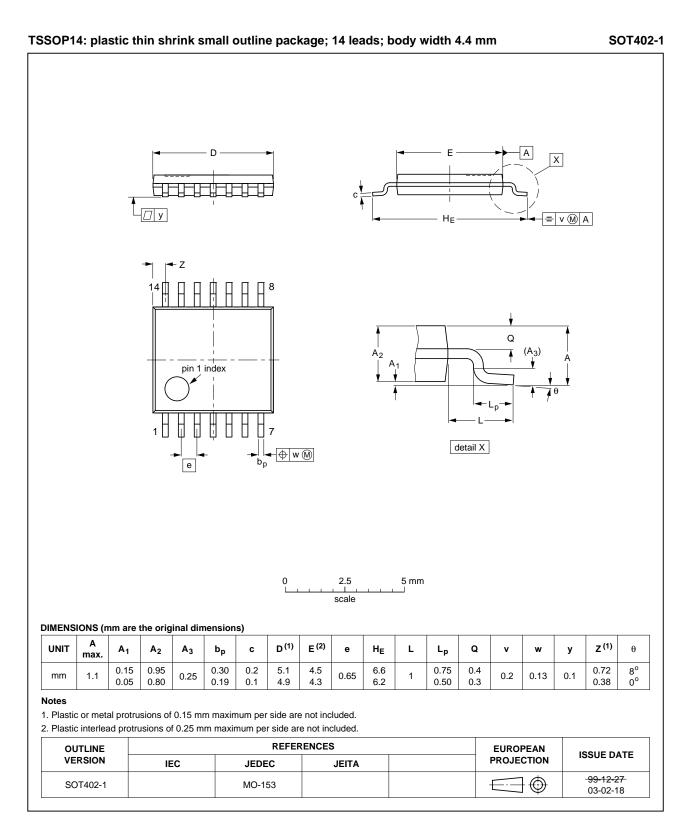


Fig 17. Package outline SOT337-1 (SSOP14)

**Quad 2-input NAND Schmitt trigger** 



#### Fig 18. Package outline SOT402-1 (TSSOP14)

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## **17. Abbreviations**

| Description<br>Complementary Metal-Oxide Semiconductor |
|--|
| Complementary Metal-Oxide Semiconductor                |
|  |
| Device Under Test                                      |
| ElectroStatic Discharge                                |
| Human Body Model                                       |
| Low-power Schottky Transistor-Transistor Logic         |
| Machine Model  |
| Transistor-Transistor Logic                            |
|  |

## 18. Revision history

| Table 12. Revision hist | ory  |                               |                     |                             |
|-------------------------|--|-------------------------------|---------------------|-----------------------------|
| Document ID             | Release date   | Data sheet status             | Change notice       | Supersedes                  |
| 74HC_HCT132 v.3         | 20120830   | Product data sheet            | -                   | 74HC_HCT132_CNV v.2         |
| Modifications:          | <ul> <li>The format of this data<br/>of NXP Semiconduct</li> </ul> |                               | gned to comply with | the new identity guidelines |
|                         | <ul> <li>Legal texts have be</li> </ul>                            | en adapted to the new co      | mpany name where    | appropriate.                |
|                         | <ul> <li>Figure 14 added (ty</li> </ul>                            | pical K-factor for relaxation | on oscillator).     |                             |
| 74HC_HCT132_CNV v.2     | 19970826   | Product specification         | -                   | -                           |

### **19. Legal information**

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| Document status[1][2]          | Product status <sup>[3]</sup> | Definition  |
|--------------------------------|-------------------------------|---|
| Objective [short] data sheet   | Development                   | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification                 | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production                    | This document contains the product specification.                                     |

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[2] The term 'short data sheet' is explained in section "Definitions".

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#### Quad 2-input NAND Schmitt trigger

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### Quad 2-input NAND Schmitt trigger

### 21. Contents

| 1    | General description 1              |
|------|------------------------------------|
| 2    | Features and benefits 1            |
| 3    | Applications 1                     |
| 4    | Ordering information 2             |
| 5    | Functional diagram 2               |
| 6    | Pinning information 3              |
| 6.1  | Pinning 3                          |
| 6.2  | Pin description 3                  |
| 7    | Functional description 3           |
| 8    | Limiting values 4                  |
| 9    | Recommended operating conditions 4 |
| 10   | Static characteristics 5           |
| 11   | Dynamic characteristics 6          |
| 12   | Waveforms 7                        |
| 13   | Transfer characteristics           |
| 14   | Transfer characteristics waveforms |
| 15   | Application information 10         |
| 16   | Package outline 13                 |
| 17   | Abbreviations 17                   |
| 18   | Revision history 17                |
| 19   | Legal information 18               |
| 19.1 | Data sheet status 18               |
| 19.2 | Definitions 18                     |
| 19.3 | Disclaimers                        |
| 19.4 | Trademarks                         |
| 20   | Contact information 19             |
| 21   | Contents 20                        |

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